

N-Channel Power MOSFET

40V, 121A, 3.3mΩ

FEATURES

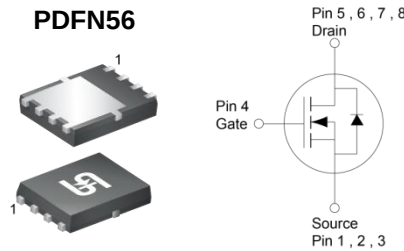
- Low $R_{DS(ON)}$ to minimize conductive losses
- Low gate charge for fast power switching
- 100% UIS and R_g tested.
- 175°C Operating Junction Temperature
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS

PARAMETER	VALUE	UNIT
V_{DS}	40	V
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	3.3
Q_g	77	nC

APPLICATIONS

- BLDC Motor Control
- Battery Power Management
- DC-DC converter
- Secondary Synchronous Rectification



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 1)	I_D	$T_C = 25^\circ\text{C}$	A
		$T_A = 25^\circ\text{C}$	
Pulsed Drain Current	I_{DM}	484	A
Single Pulse Avalanche Current (Note 2)	I_{AS}	36	A
Single Pulse Avalanche Energy (Note 2)	E_{AS}	194	mJ
Total Power Dissipation	P_D	$T_C = 25^\circ\text{C}$	W
		$T_C = 125^\circ\text{C}$	
Total Power Dissipation	P_D	$T_A = 25^\circ\text{C}$	W
		$T_A = 125^\circ\text{C}$	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +175	$^\circ\text{C}$

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	1.4	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	48	$^\circ\text{C/W}$

Thermal Performance Note: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. The $R_{\theta JA}$ limit presented here is based on mounting on a 1 in² pad of 2 oz copper.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	40	--	--	V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu A$	$V_{GS(TH)}$	2	2.9	4	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I_{GSS}	--	--	± 100	nA
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 40V$	I_{DSS}	--	--	1	μA
	$V_{GS} = 0V, V_{DS} = 40V$ $T_J = 125^{\circ}C$		--	--	100	
Drain-Source On-State Resistance (Note 3)	$V_{GS} = 10V, I_D = 21A$	$R_{DS(on)}$	--	2.4	3.3	m Ω
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_D = 21A$	g_{fs}	--	64	--	S
Dynamic (Note 4)						
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 20V,$ $I_D = 21A$	Q_g	--	77	-	nC
Gate-Source Charge		Q_{gs}	--	23	--	
Gate-Drain Charge		Q_{gd}	--	19	--	
Input Capacitance	$V_{GS} = 0V, V_{DS} = 20V$ $f = 1.0MHz$	C_{iss}	--	5022	--	pF
Output Capacitance		C_{oss}	--	484	--	
Reverse Transfer Capacitance		C_{rss}	--	250	--	
Gate Resistance	$f = 1.0MHz$	R_g	0.5	1.5	3	Ω
Switching (Note 4)						
Turn-On Delay Time	$V_{GS} = 10V, V_{DS} = 20V,$ $I_D = 21A, R_G = 2\Omega$	$t_{d(on)}$	--	7	--	ns
Turn-On Rise Time		t_r	--	22	--	
Turn-Off Delay Time		$t_{d(off)}$	--	35	--	
Turn-Off Fall Time		t_f	--	17	--	
Source-Drain Diode						
Forward Voltage (Note 3)	$V_{GS} = 0V, I_S = 21A$	V_{SD}	--	--	1	V
Reverse Recovery Time	$I_S = 21A,$	t_{rr}	--	26	--	ns
Reverse Recovery Charge	$di/dt = 100A/\mu s$	Q_{rr}	--	19	--	nC

Notes:

- Silicon limited current only.
- $L = 0.3\text{mH}$, $V_{GS} = 10V$, $V_{DD} = 25V$, $R_G = 25\Omega$, $I_{AS} = 36A$, Starting $T_J = 25^\circ\text{C}$
- Pulse test: Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- Switching time is essentially independent of operating temperature.

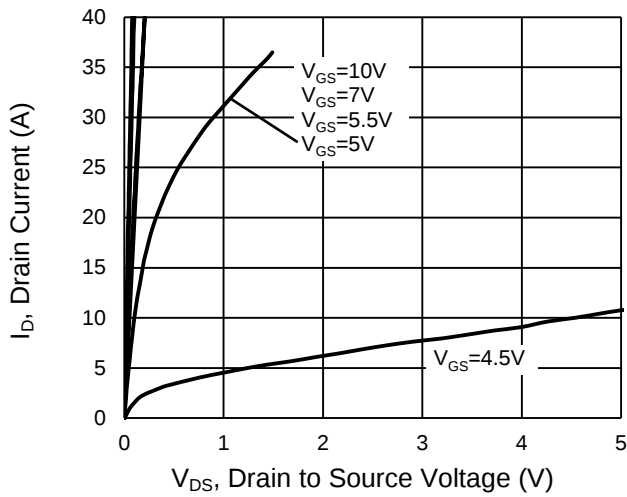
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM033NB04CR RLG	PDFN56	2,500pcs / 13" Reel

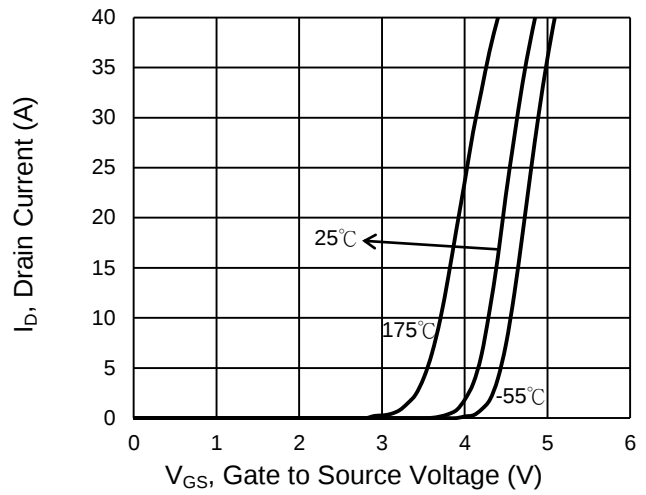
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

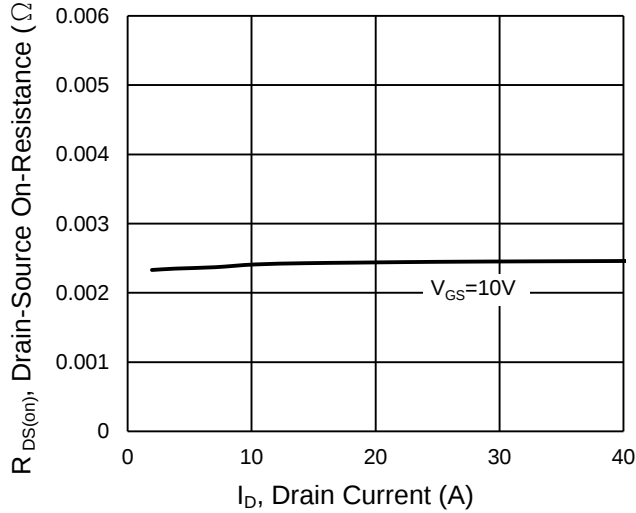
Output Characteristics



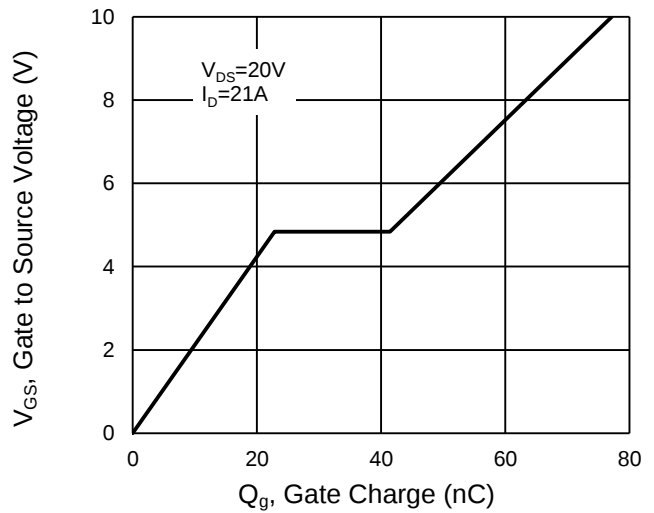
Transfer Characteristics



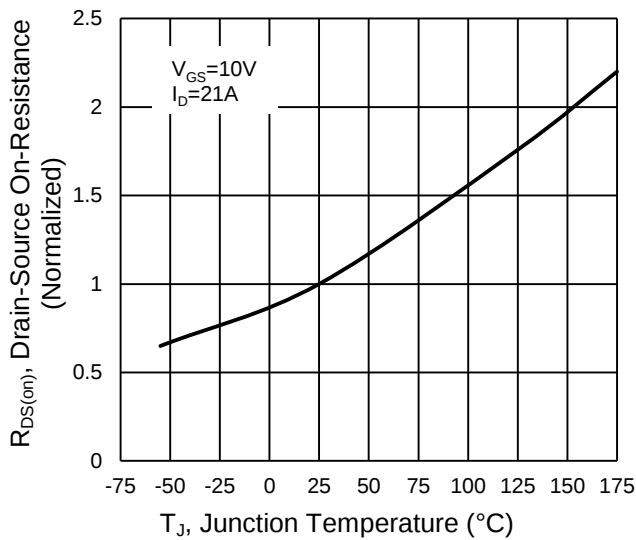
On-Resistance vs. Drain Current



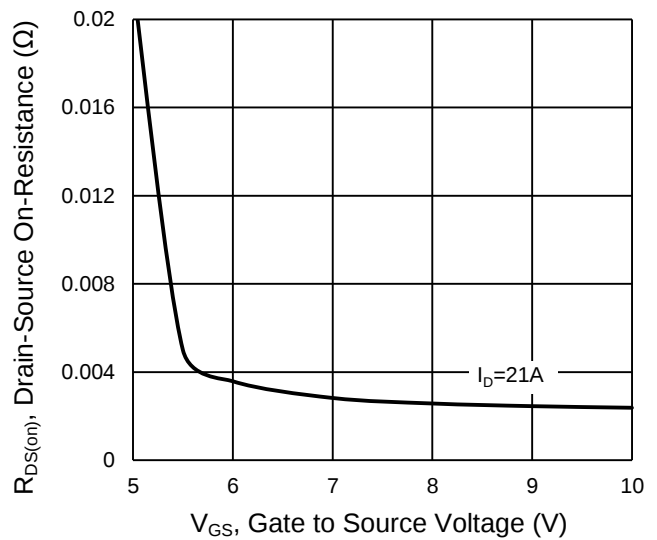
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature

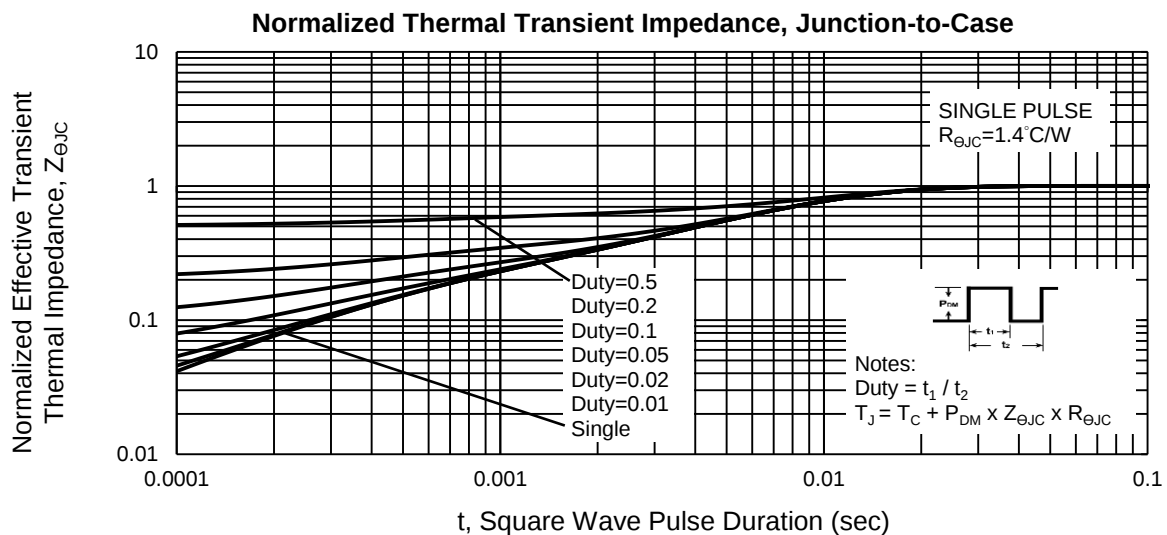
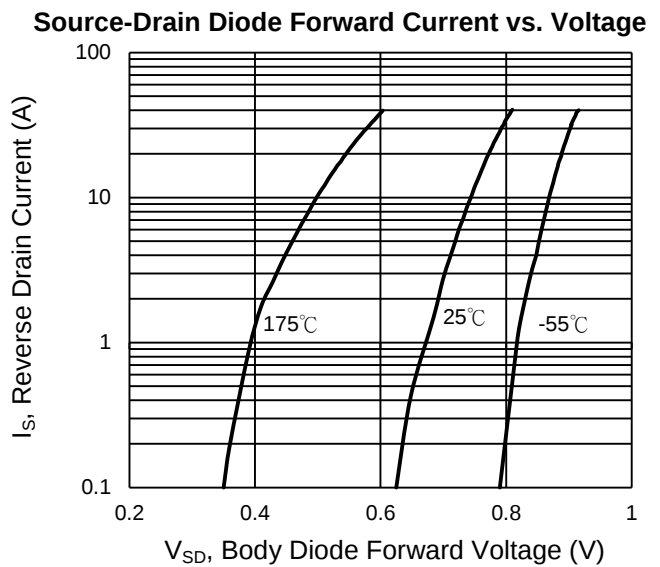
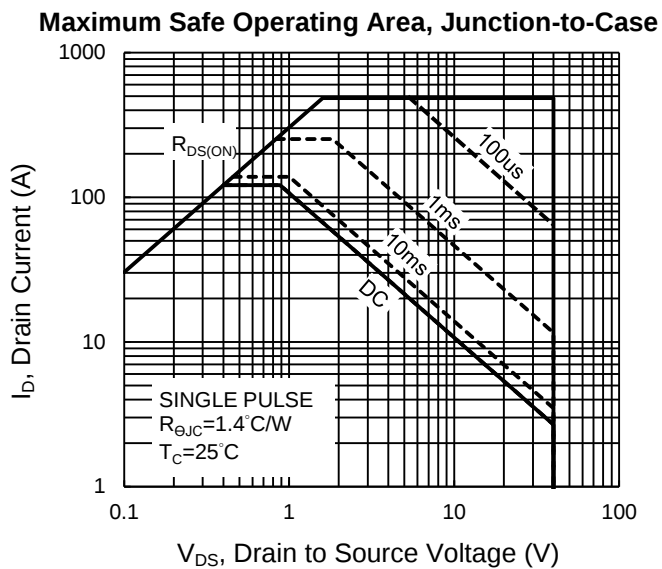
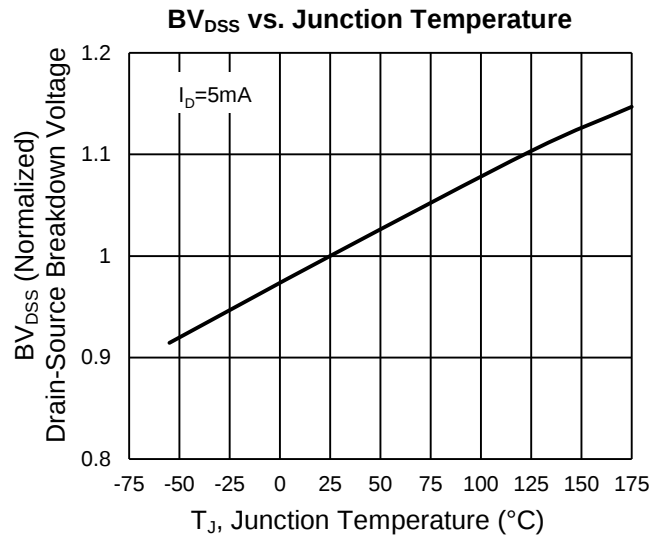
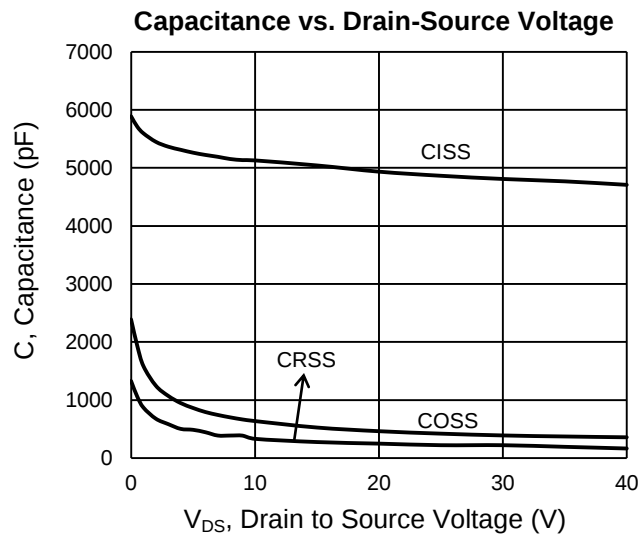


On-Resistance vs. Gate-Source Voltage



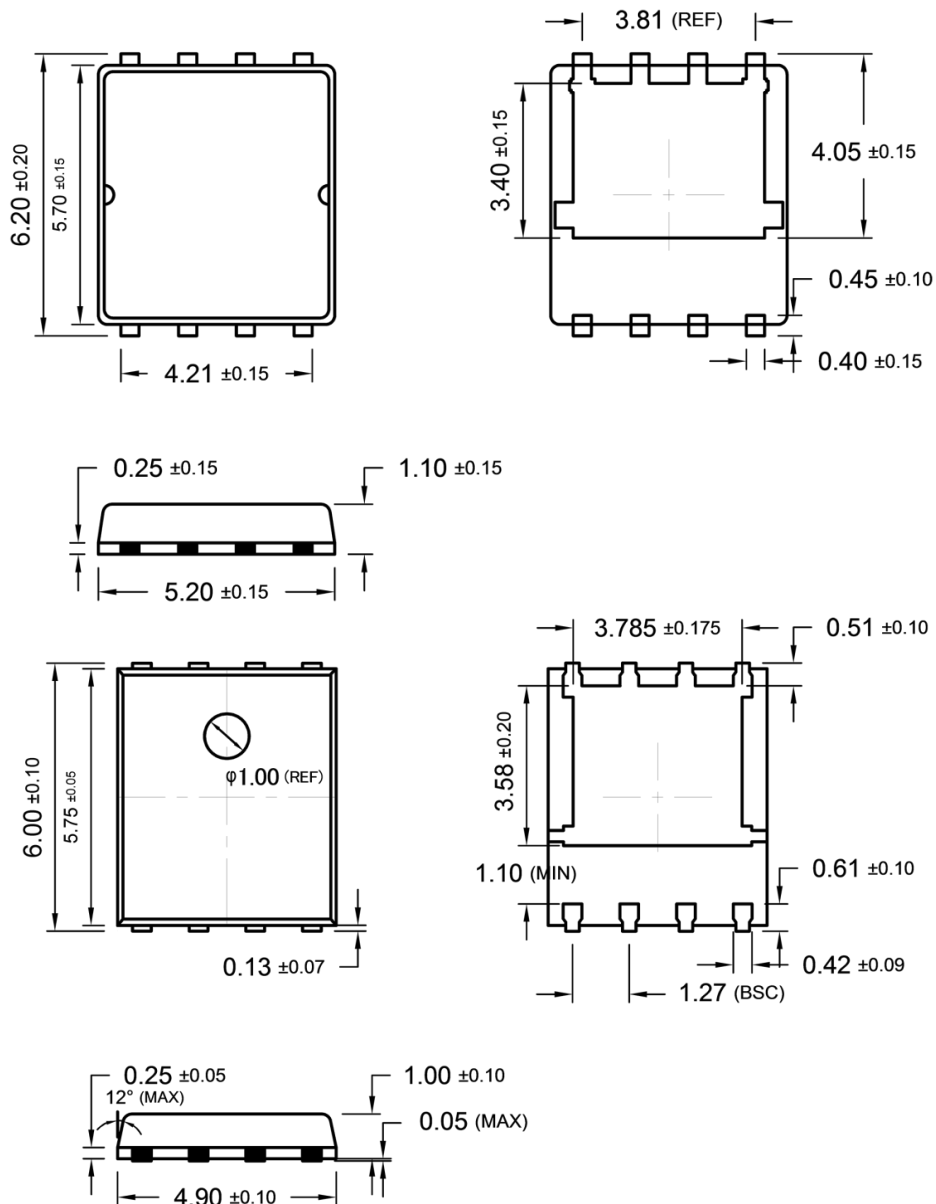
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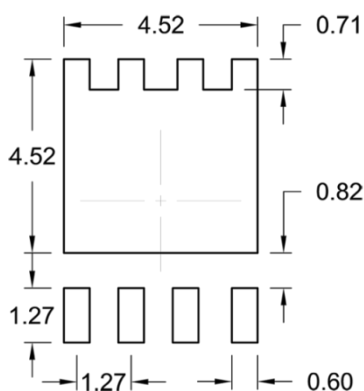


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

PDFN56



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



G = Halogen Free
Y = Year Code
WW = Week Code (01~52)
F = Factory Code

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